

## NTE398 Silicon PNP Transistor TV Vertical Output (Compl to NTE375)

**Absolute Maximum Ratings:** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Collector–Base Voltage, $V_{CBO}$	200V
Collector–Emitter Voltage, $V_{CEO}$	150V
Emitter–Base Voltage, $V_{EBO}$	5V
Collector Current, $I_C$	
Continuous	2A
Pulsed (Note 1)	3A
Collector Dissipation ( $T_C = +25^\circ\text{C}$ ), $P_C$	25W
Operating Junction Temperature, $T_J$	$+150^\circ\text{C}$
Storage Temperature Range, $T_{stg}$	$-55^\circ$ to $+150^\circ\text{C}$

Note 1. Pulse Width  $\leq 10\text{ms}$ , Duty Cycle  $\leq 50\%$ .

**Electrical Characteristics:** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 150\text{V}$ , $I_E = 0$	–	–	50	$\mu\text{A}$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = 4\text{V}$ , $I_C = 0$	–	–	50	$\mu\text{A}$
DC Current Gain	$h_{FE}$	$V_{CE} = 10\text{V}$ , $I_C = 400\text{mA}$ , Note 2	60	–	120	
Gain Bandwidth Product	$f_T$	$V_{CE} = 10\text{V}$ , $I_C = 400\text{mA}$ , Note 2	–	5	–	MHz
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 500\text{A}$ , $I_B = 50\text{mA}$	–	–	1.0	V

Note 2. Pulse Width  $\leq 350\mu\text{s}$ , Duty Cycle  $\leq 25\%$ /Pulsed.

